
Contents

Preface	V
1 Basic Properties of ZnO, GaN, and Related Materials	
<i>T. Hanada</i>	1
1.1 Introduction	1
1.2 Crystal Structure	1
1.2.1 Crystal Structure of Related Materials	1
1.2.2 Hexagonal Lattice Vectors and Planes	4
1.3 Elastic Strain	6
1.3.1 Elastic Constants and Elastic Energy Density	6
1.3.2 Strain in Hexagonal- and Cubic-Structure Films	8
1.4 Electronic Structure	10
1.4.1 Bandgap and Band-Edge Electronic Structure	10
1.4.2 Bir-Pikus Hamiltonian	12
1.4.3 Valence Band-Edge and Bandgap of Strained ZnO	15
1.4.4 Exciton Binding Energy	17
References	18
2 Solvothermal Growth of ZnO and GaN	
<i>D. Ehrentraut, F. Orito, Y. Mikawa, and T. Fukuda</i>	21
2.1 Introduction	21
2.2 Hydrothermal Growth	23
2.2.1 Hydrothermal Growth Technology for ZnO	23
2.2.2 Growth Mechanism	28
2.2.3 Liquid Phase Epitaxy and Growth of Microcrystals	30
2.2.4 Properties of Hydrothermal ZnO	32
2.2.5 Future Developments	46
2.3 Ammonothermal Growth	47
2.3.1 A Brief Review of the Growth of GaN Bulk Crystals	47
2.3.2 Ammonothermal Growth Technology for GaN	48

VIII Contents

2.3.3	Properties of Ammonothermal GaN	54
2.3.4	Prospects for Ammonothermal GaN	60
References	62

3 Growth of ZnO and GaN Films

<i>J. Chang, S.-K. Hong, K. Matsumoto, H. Tokunaga, A. Tachibana,</i>		
<i>S.W. Lee, and M.-W. Cho</i>		67
3.1	MBE and PLD of ZnO and Related Materials	67
<i>J. Chang and S.-K. Hong</i>		67
3.1.1	Introduction	67
3.1.2	General Features of the PAMBE	68
3.1.3	PAMBE of ZnO Thin Films on Various Substrates	71
3.1.4	Other Growth Factors in PAMBE of ZnO and their Properties	84
3.1.5	Bandgap Engineering of ZnO-Based Alloys Grown by PAMBE	101
3.1.6	General Features of the PLD	112
3.1.7	Droplet Formation in the PLD Process	113
3.1.8	Growth of ZnO Thin Films on Various Substrates by PLD	114
3.1.9	Bandgap Engineering of ZnO-based Alloys Grown by PLD	124
3.2	MOCVD Growth of GaN and Related Materials	130
<i>K. Matsumoto, H. Tokunaga, and A. Tachibana</i>		130
3.2.1	Introduction	130
3.2.2	Heteroepitaxy of GaN and Alloys: Materials Property and Growth Condition	130
3.2.3	Reaction Mechanism: Experiments and Theory	140
3.2.4	Growth Equipment	146
3.2.5	Atmospheric Pressure Reactor for Nitride	149
3.3	HVPE of GaN and Related Materials	156
<i>S.W. Lee and M.-W. Cho</i>		156
3.3.1	Introduction	156
3.3.2	Thermodynamic Considerations of HVPE of GaN	156
3.3.3	Growth System	160
3.3.4	Thick GaN Film Growth	163
3.3.5	Fabrication of Free-Standing GaN Substrate	166
3.3.6	Other III Nitrides Grown by HVPE	174
References	176

4 Control of Polarity and Application to Devices

<i>J.S. Park and S.-K. Hong</i>		185
4.1	Introduction	185
4.2	Polarity	186
4.3	Spontaneous and Piezoelectric Polarization	188

4.4	Determination of Polarity	191
4.4.1	Determination Based on Diffraction	192
4.4.2	Determination Based on Spectroscopy	195
4.4.3	Determination Based on Microscopy	198
4.4.4	Determination Based on Differences in Etching and Growth Rates	201
4.5	Control of Polarity	205
4.5.1	Polarity Control of GaN Films	205
4.5.2	Polarity Control of ZnO Films	207
4.5.3	Polarity of AlN and InN Films	210
4.6	Effects of Polarity on Material Properties	211
4.7	Device Applications of Polarization Induced Properties	213
4.7.1	Electronic Devices	214
4.7.2	Nonlinear Optical Devices	216
	References	218

5 Growth of Nonpolar GaN and ZnO Films

	<i>S.-K. Hong and H.-J. Lee</i>	225
5.1	Introduction	225
5.2	Polar Surface, Nonpolar Surface, and Heterostructures	226
5.3	Growth of Nonpolar GaN Films	229
5.3.1	M-plane GaN Films	229
5.3.2	A-plane GaN Films	233
5.3.3	Semipolar GaN Films	238
5.4	Lateral Epitaxial Overgrowth of Nonpolar GaN Films	239
5.4.1	LEO of A-plane GaN	239
5.4.2	LEO of M-plane GaN	245
5.5	Growth of Nonpolar ZnO Films	247
5.5.1	A-plane ZnO Films	247
5.5.2	M-plane ZnO Films	254
	References	258

6 Structural Defects in GaN and ZnO

	<i>S.-K. Hong and H.K. Cho</i>	261
6.1	Introduction	261
6.2	Dislocation and Stacking Faults	262
6.2.1	Dislocations	262
6.2.2	Misfit and Threading Dislocations	264
6.2.3	Dislocation in Wurtzite Structure	265
6.2.4	Stacking Fault in Wurtzite Structure	266
6.3	TEM of Defects in GaN and ZnO Films	267
6.3.1	Defect Contrast in TEM	267
6.3.2	Analysis of Threading Dislocation by Cross-sectional TEM	269
6.3.3	Analysis of Threading Dislocation by Plan-View TEM ...	274

6.3.4	Misfit Dislocation	277
6.3.5	Nanopipe	281
6.3.6	Stacking Fault	281
6.3.7	Inversion Domain Boundary	285
6.4	Dislocation Reduction of Epitaxial Films by Process	286
6.4.1	Defects in Epitaxial Lateral Overgrowth (ELOG)	286
6.4.2	Defects in PENDEO Epitaxy (PE)	293
6.4.3	Defects in Facet-Controlled Epitaxial Lateral Overgrowth (FACELO)	297
6.4.4	Defects in Other Overgrowth Techniques	299
6.4.5	Other Growth and Process Techniques for Defect Reduction	302
References	306

7 Optical Properties of GaN and ZnO

<i>J.-H. Song</i>	311
7.1	Introduction	311
7.1.1	Basics	313
7.1.2	Valence Band Structure	313
7.2	Emission Properties of GaN	315
7.2.1	Band Edge Emissions	315
7.2.2	Defect-Related Emissions	320
7.2.3	Deep Level Emissions	323
7.2.4	Emission Properties of InGaN/GaN Quantum Wells	324
7.3	Emission Properties of ZnO	331
7.3.1	Band Edge Emissions	332
7.3.2	Defect-Related Emissions	334
7.3.3	Deep-Level Emissions	338
7.3.4	Emission Properties of MgZnO/ZnO Quantum Wells ...	338
7.4	Emission Properties of Nonpolar GaN and ZnO	339
7.4.1	Polarized Emission	340
7.4.2	Strain Effects	340
7.5	Raman Scattering Properties of GaN and ZnO	344
7.5.1	Strain Effects	344
7.5.2	Carrier Concentration	346
References	349

8 Electrical Properties of GaN and ZnO

<i>D.-C. Oh</i>	355
8.1	Introduction	355
8.2	Ohmic Contacts to GaN and ZnO	356
8.2.1	Principle of Ohmic Contact	356
8.2.2	Ohmic Contacts to GaN	358
8.2.3	Ohmic Contacts to ZnO	363
8.3	Schottky Contacts to GaN and ZnO	366
8.3.1	Principle of Schottky Contact	366

8.3.2	Schottky Contacts to GaN.....	369
8.3.3	Schottky Contacts to ZnO.....	373
8.4	Electrical Properties	382
8.4.1	Electron Transport Mechanism.....	382
8.4.2	Electrical Properties of GaN	383
8.4.3	Electrical Properties of ZnO	391
8.5	Deep Levels of GaN and ZnO	397
8.5.1	Characterization of Deep Levels	397
8.5.2	Deep Levels in GaN	399
8.5.3	Deep Levels in ZnO	405
	References	411

9 GaN and ZnO Light Emitters

<i>J.-S. Ha</i>	415
9.1 Introduction	415
9.2 Light-Emitting Diodes Basic	416
9.3 Light-Emitting Diodes Based on GaN	419
9.3.1 Issues for High Internal Quantum Efficiency	419
9.3.2 Issues for High External Quantum Efficiency	429
9.3.3 Packaging	437
9.3.4 Vertical Light-Emitting Diode	440
9.4 Light-Emitting Diodes Based on ZnO	444
9.4.1 Hybrid LED	444
9.4.2 ZnO LEDs with Homo p-n Junction	449
References	454

10 ZnO and GaN Nanostructures and their Applications

<i>S.H. Lee</i>	459
10.1 Introduction	459
10.2 Control of ZnO and GaN Nanostructures	460
10.2.1 Synthetic Methods	460
10.2.2 Processing and Assembly	465
10.3 ZnO and GaN Nanostructures for Photonic Device Applications.....	469
10.3.1 Optical Cavity and Lasing	470
10.3.2 Nanostructure-Based LED	479
10.4 ZnO and GaN Nanostructures for Electronic and Sensing Device Applications.....	485
10.4.1 Field Effect Transistors (FET)	485
10.4.2 Light Sensor	492
10.4.3 Gas and Solution Sensor	496
10.4.4 Biosensor	498
References	503

Index	507
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